

DUAL N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
50V	3.5Ω @ V _{GS} = 10V	200mA

Description and Applications

This MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Load Switch

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at <https://www.diodes.com/products/automotive/automotive-products/>.**
- **This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability. <https://www.diodes.com/quality/product-definitions/>**
- **An Automotive-Compliant Part is Available Under Separate Datasheet ([BSS138DWQ](#))**

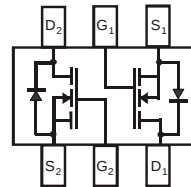
Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 ②③
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)

SOT363 (Standard)



Top View



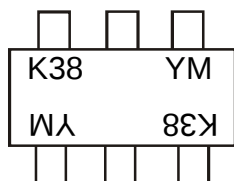
Top View
Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
BSS138DW-7-F	SOT363 (Standard)	3000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



K38 = Product Type Marking Code
YM = Date Code Marking
Y or $\bar{Y}$ = Year (ex: 1 = 2021)
M or $\bar{M}$ = Month (ex: 9 = September)

Date Code Key

Year	2007	...	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	U	...	I	J	K	L	M	N	O	P	R	S

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	50	V
Drain-Gate Voltage (Note 7)	V _{DGR}	50	V
Gate-Source Voltage	V _{GSS}	±20	V
Drain Current (Note 5)	I _D	200	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	200	mW
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	625	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	50	75	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	0.5	μA	V _{DS} = 50V, V _{GS} = 0V
Gate-Body Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(TH)}	0.5	1.2	1.5	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	1.4	3.5	Ω	V _{GS} = 10V, I _D = 0.22A
Forward Transconductance	g _{FS}	100	—	—	mS	V _{DS} = 25V, I _D = 0.2A, f = 1.0kHz
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	—	50	pF	V _{DS} = 10V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	—	25	pF	
Reverse Transfer Capacitance	C _{rss}	—	—	8.0	pF	
Turn-On Delay Time	t _{D(ON)}	—	—	20	ns	V _{DD} = 30V, I _D = 0.2A, R _{GEN} = 50Ω
Turn-Off Delay Time	t _{D(OFF)}	—	—	20	ns	

- Notes:
5. Device mounted on FR-4 PCB, 1 inch × 0.85 inch × 0.062 inch; pad layout as shown in Diodes Incorporated's package outline PDFs, which can be found on our website at <http://www.diodes.com/package-outlines.html>.
 6. Short duration pulse test used to minimize self-heating effect.
 7. R_{GS} ≤ 20kΩ.
 8. Guaranteed by design. Not subject to product testing.

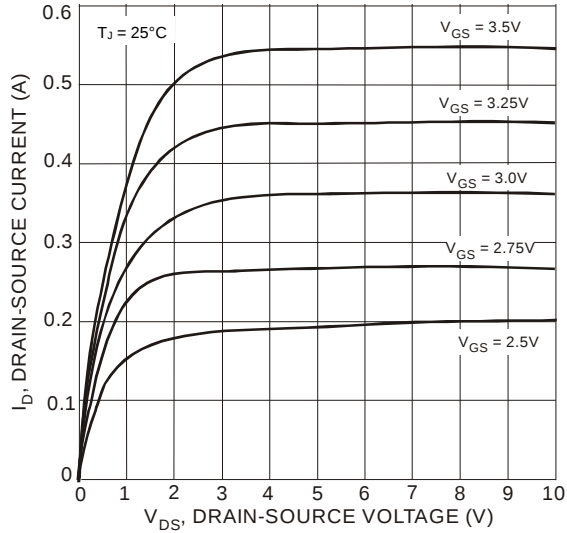


Fig. 1 Drain-Source Current vs. Drain-Source Voltage

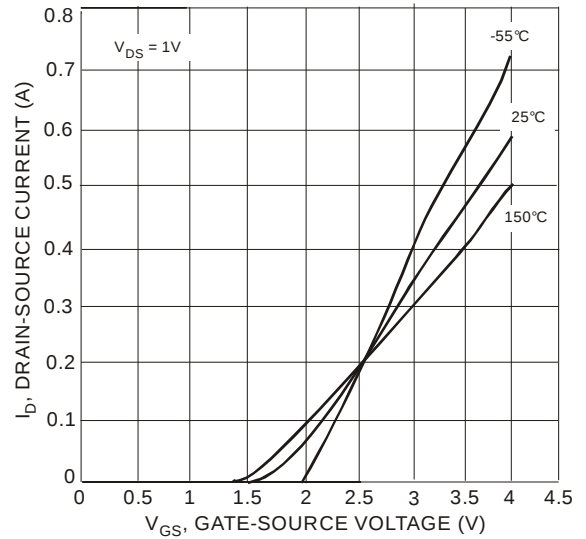


Fig. 2 Transfer Characteristics

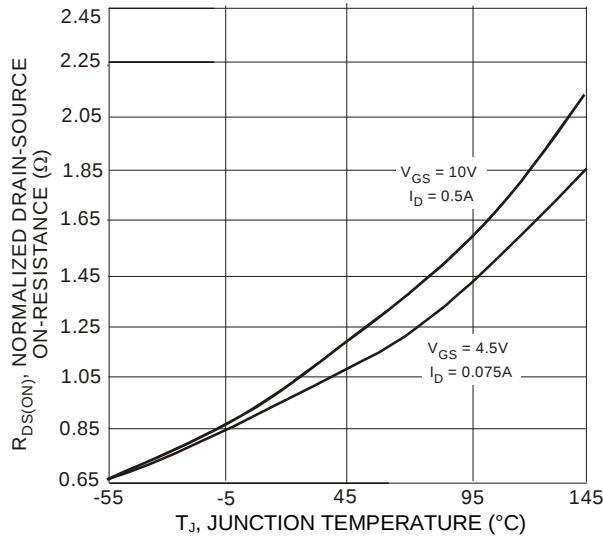


Fig. 3 Drain-Source On Resistance vs. Junction Temperature

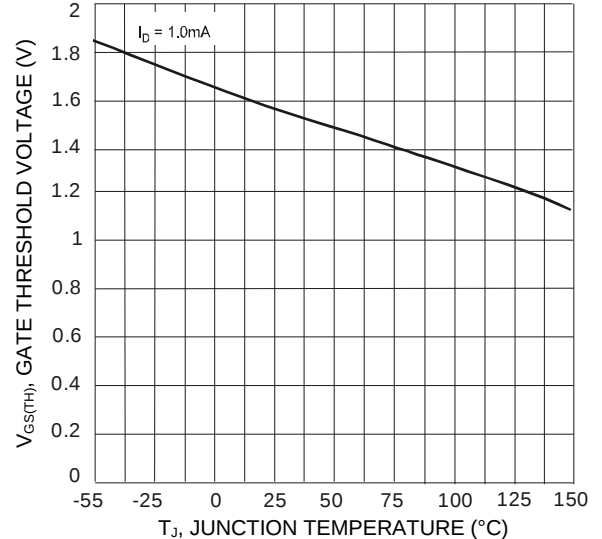


Fig. 4 Gate Threshold Voltage vs. Junction Temperature

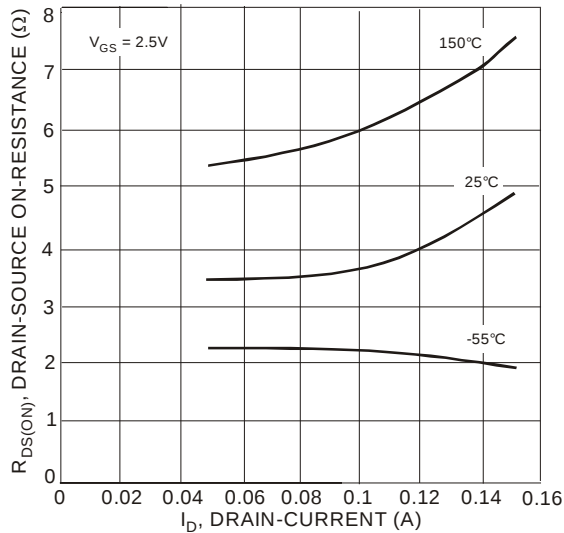


Fig. 5 Drain-Source On-Resistance vs. Drain-Current

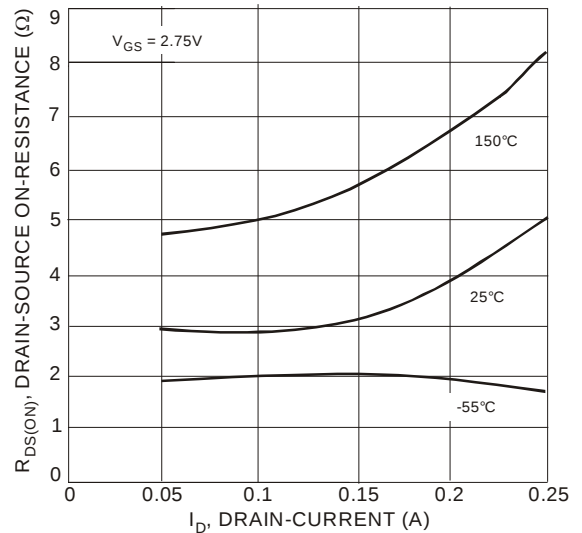
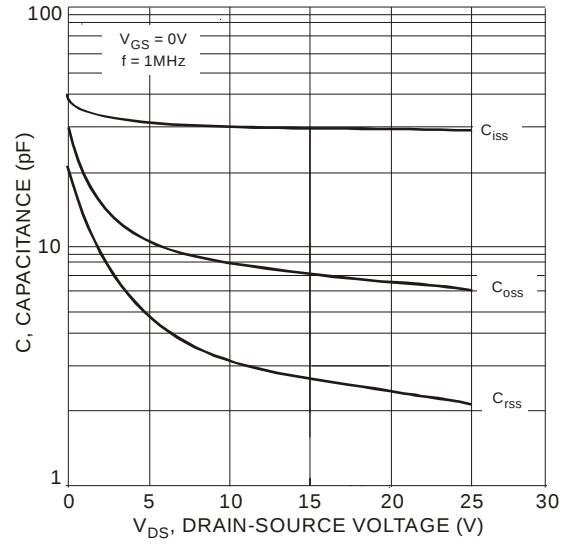
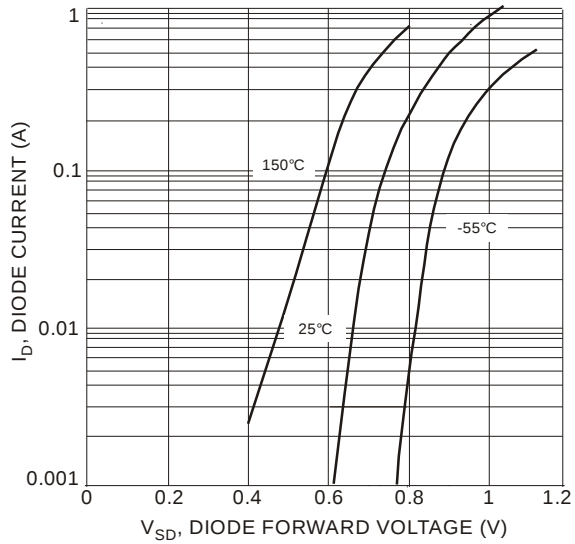
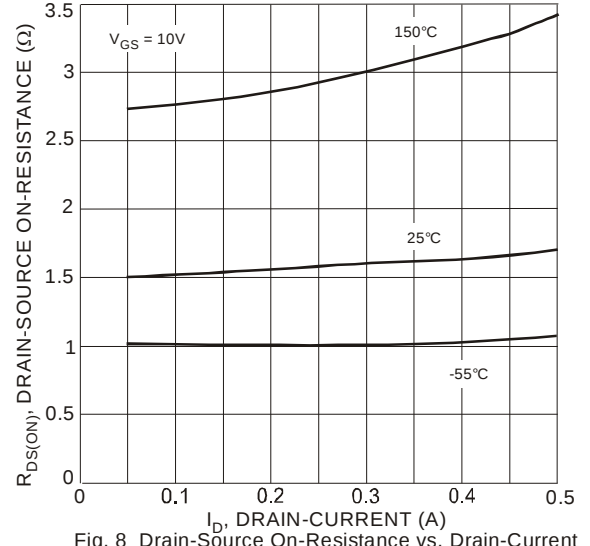
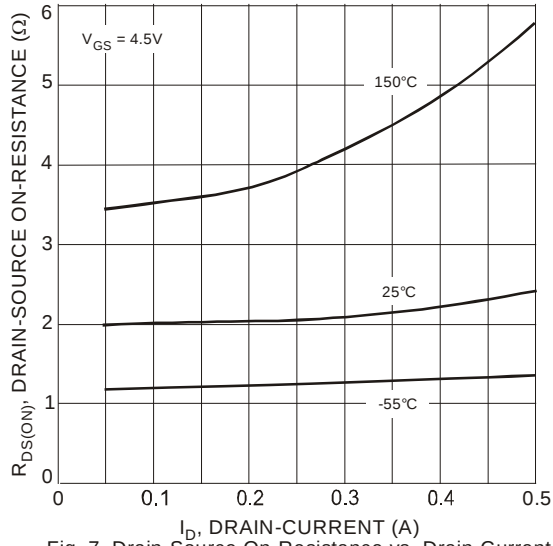


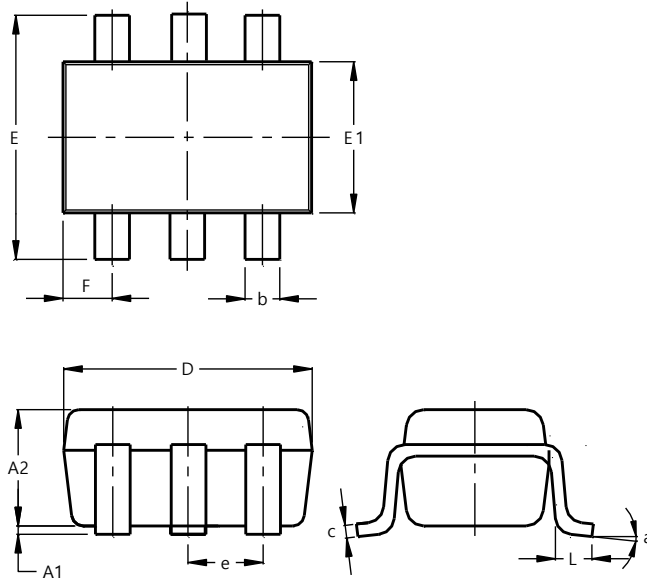
Fig. 6 Drain-Source On-Resistance vs. Drain-Current



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT363 (Standard)

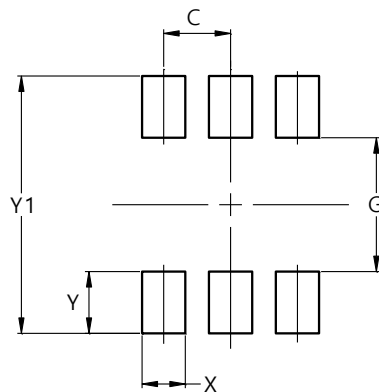


SOT363 (Standard)			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.80	1.00	0.90
b	0.10	0.35	0.225
c	0.08	0.22	0.15
D	1.80	2.20	2.00
E	2.00	2.45	2.225
E1	1.15	1.35	1.25
e	--	--	0.65
F	0.25	0.45	0.35
L	0.25	0.46	0.355
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT363 (Standard)



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500